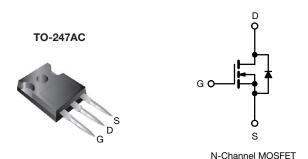


# **Power MOSFET**



PRODUCT SUMMARY			
V <sub>DS</sub> (V) 200			
R <sub>DS(on)</sub> (Ω)	V <sub>GS</sub> = 10 V 0.055		
Q <sub>g</sub> (max.) (nC)	230		
Q <sub>gs</sub> (nC)	42		
Q <sub>gd</sub> (nC)	110		
Configuration	Single		

### **FEATURES**

- Dynamic dV/dt rating
- Repetitive avalanche rated
- · Isolated central mounting hole
- · Fast switching
- · Ease of paralleling
- Simple drive requirements
- Material categorization: for definitions of compliance please see <a href="https://www.vishav.com/doc?99912"><u>www.vishav.com/doc?99912</u></a>

#### Note

\* This datasheet provides information about parts that are RoHS-compliant and / or parts that are non RoHS-compliant. For example, parts with lead (Pb) terminations are not RoHS-compliant. Please see the information / tables in this datasheet for details

## **DESCRIPTION**

Third generation Power MOSFETs from Vishay provide the designer with the best combination of fast switching, ruggedized device design, low on-resistance and cost-effectiveness.

The TO-247AC package is preferred for commercial-industrial applications where higher power levels preclude the use of TO-220AB devices. The TO-247AC is similar but superior to the earlier TO-218 package because of its isolated mouting hole. It also provides greater creepage distance between pins to meet the requirements of most safety specifications.

ORDERING INFORMATION		
Package	TO-247AC	
Lead (Pb)-free	IRFP260PbF	

PARAMETER			SYMBOL	LIMIT	UNIT
Drain-source voltage			$V_{DS}$	200	V
Gate-source voltage			$V_{GS}$	± 20	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \
Continuous drain current	\/ at 10 \/	T <sub>C</sub> = 25 °C	1	46	
Continuous drain current	$V_{GS}$ at 10 V $T_C = 100 ^{\circ}$ C		I <sub>D</sub>	29	Α
Pulsed drain current <sup>a</sup>			I <sub>DM</sub>	180	
Linear derating factor				2.2	W/°C
Single pulse avalanche energy b			E <sub>AS</sub>	1000	mJ
Repetitive avalanche current <sup>a</sup>			I <sub>AR</sub>	46	А
Repetitive avalanche energy <sup>a</sup>			E <sub>AR</sub>	28	mJ
Maximum power dissipation $T_C = 25  ^{\circ}C$			$P_{D}$	280	W
Peak diode recovery dV/dt c			dV/dt	5.0	V/ns
Operating junction and storage temperature range			T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
Soldering recommendations (peak temperature) d for 10 s				300	
Marathan Indian				10	lbf ⋅ in
Mounting torque	6-32 or M3 screw			1.1	N⋅m

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b.  $V_{DD}$  = 50 V, starting  $T_J$  = 25 °C, L = 708  $\mu$ H,  $R_g$  = 25  $\Omega$ ,  $I_{AS}$  = 46 A (see fig. 12)
- c.  $I_{SD} \leq$  46 A,  $dI/dt \leq$  230 A/ $\mu$ s,  $V_{DD} \leq$   $V_{DS}$ ,  $T_{J} \leq$  150 °C
- d. 1.6 mm from case



# Vishay Siliconix

THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum junction-to-ambient	R <sub>thJA</sub>	-	40	
Case-to-sink, flat, greased surface	R <sub>thCS</sub>	0.24	-	°C/W
Maximum junction-to-case (drain)	R <sub>thJC</sub>	-	0.45	

PARAMETER	SYMBOL	TEST (	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static							
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 2$	50 μΑ	200		-	V
V <sub>DS</sub> temperature coefficient	$\Delta V_{DS}/T_{J}$	Reference to 25	°C, I <sub>D</sub> = 1 mA	-	0.24	-	V/°C
Gate-source threshold voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 2$	250 μA	2.0	-	4.0	V
Gate-source leakage	I <sub>GSS</sub>	$V_{GS} = \pm 20 \text{ V}$		-	-	± 100	nA
7		$V_{DS} = 200 \text{ V}, V_{GS}$	<sub>S</sub> = 0 V	-	-	25	_
Zero gate voltage drain current	I <sub>DSS</sub>	$V_{DS} = 160 \text{ V}, V_{GS}$	<sub>S</sub> = 0 V, T <sub>J</sub> = 125 °C	-	-	250	μA
Drain-source on-state resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 28 A <sup>b</sup>	-	-	0.055	Ω
Forward transconductance	9 <sub>fs</sub>	$V_{DS} = 50 \text{ V}, I_{D} = 100 \text{ V}$	28 A <sup>b</sup>	24	-	-	S
Dynamic							
Input capacitance	C <sub>iss</sub>	$V_{GS} = 0 V$		-	5200	-	
Output capacitance	C <sub>oss</sub>	$V_{DS} = 25 \text{ V},$		-	1200	-	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1.0 MHz, see	fig. 5	-	310	-	
Total gate charge	Qg	$V_{GS} = 10 \text{ V}$ $I_D = 46 \text{ A}, V_{DS} = 160 \text{ V},$ see fig. 6 and 13 b		-	-	230	
Gate-source charge	Q <sub>gs</sub>			-	-	42	nC
Gate-drain charge	Q <sub>gd</sub>			-	-	110	1
Turn-on delay time	t <sub>d(on)</sub>	·		-	23	-	ns ns
Rise time	t <sub>r</sub>	$V_{DD} = 100 \text{ V}, I_{D} =$	$V_{DD} = 100 \text{ V}, I_D = 46 \text{ A},$		120	-	
Turn-off delay time	t <sub>d(off)</sub>	$R_g$ = 4.3 $\Omega$ , $R_D$ = 2.1 $\Omega$ , see fig. 10 $^b$		-	100	-	
Fall time	t <sub>f</sub>			-	94	-	
Internal drain inductance	L <sub>D</sub>	Between lead,	D	-	5.0	-	
Internal source inductance	L <sub>S</sub>	6 mm (0.25") from package and center of die contact		-	13	-	nH
Drain-Source Body Diode Characteristic	s						
Continuous source-drain diode current	I <sub>S</sub>	MOSFET symbo		-	-	46	
Pulsed diode forward current <sup>a</sup>	I <sub>SM</sub>	showing the integral reverse p - n junction diode		-	-	180	А
Body diode voltage	$V_{SD}$	T <sub>J</sub> = 25 °C, I <sub>S</sub> = 4	46 A, V <sub>GS</sub> = 0 V <sup>b</sup>	-	-	1.8	V
Body diode reverse recovery time	t <sub>rr</sub>	T 05 00 1	10 A -11/-14 - 100 A / - h	-	390	590	ns
Body diode reverse recovery charge	Q <sub>rr</sub>	$T_J = 25  ^{\circ}\text{C}, I_F = 46  \text{A}, dI/dt = 100  \text{A/} \mu \text{s}^{\text{b}}$		-	4.8	7.2	μC
Forward turn-on time	t <sub>on</sub>	Intrinsic turn-on time is negligible (turn-on is dominated		ated by L	s and Ln)		

- a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11)
- b. Pulse width  $\leq$  300 µs; duty cycle  $\leq$  2 %



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

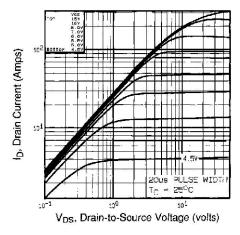


Fig. 1 - Typical Output Characteristics, T<sub>C</sub> = 25 °C

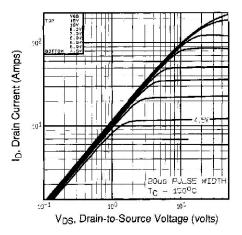


Fig. 2 - Typical Output Characteristics,  $T_C = 150$  °C

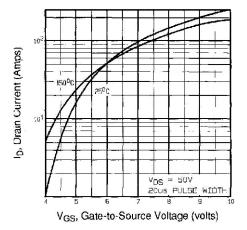


Fig. 3 - Typical Transfer Characteristics

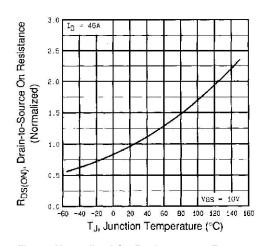


Fig. 4 - Normalized On-Resistance vs. Temperature

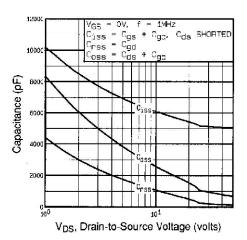


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

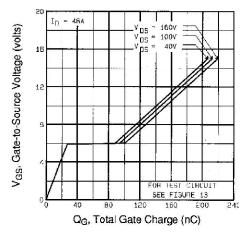


Fig. 6 - Typical Gate Charge vs. Gate-to-Source Voltage



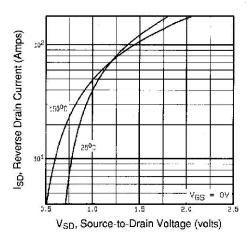


Fig. 7 - Typical Source-Drain Diode Forward Voltage

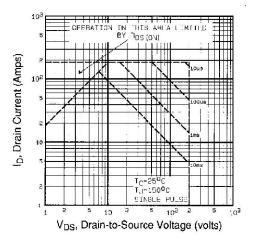


Fig. 8 - Maximum Safe Operating Area

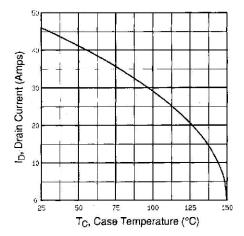


Fig. 9 - Maximum Drain Current vs. Case Temperature

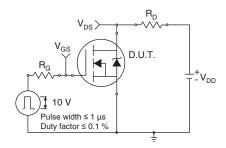


Fig. 10a - Switching Time Test Circuit

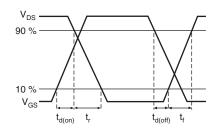


Fig. 10b - Switching Time Waveforms



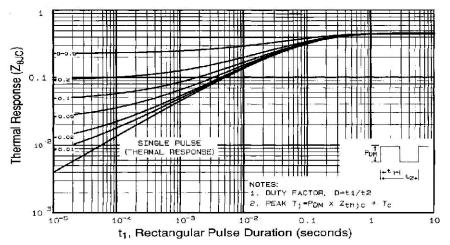


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case

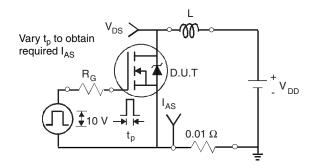


Fig. 12a - Unclamped Inductive Test Circuit

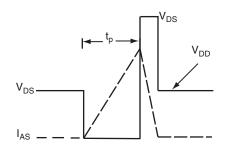


Fig. 12b - Unclamped Inductive Waveforms

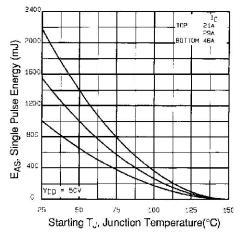


Fig. 12c - Maximum Avalanche Energy vs. Drain Current



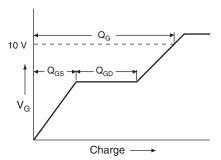


Fig. 13a - Basic Gate Charge Waveform

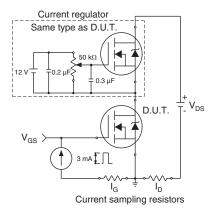
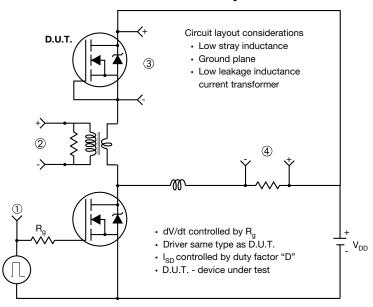


Fig. 13b - Gate Charge Test Circuit



### Peak Diode Recovery dV/dt Test Circuit



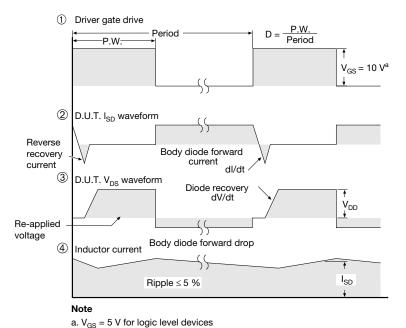


Fig. 14 - For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg?91215">www.vishay.com/ppg?91215</a>.



# **TO-247AC (High Voltage)**

### **VERSION 1: FACILITY CODE = 9**







Section C--C,D--D,E--E

	MILLIN	IETERS	
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44	BSC	
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- (7) Ø P to have a maximum draft angle of 1.5° to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

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### **VERSION 2: FACILITY CODE = Y**



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	BSC	
Øk	0.254		
L	14.20	16.25	
L1	3.71	4.29	
ØР	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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## **VERSION 3: FACILITY CODE = N**



	MILLIM	IETERS
DIM.	MIN.	MAX.
Α	4.65	5.31
A1	2.21	2.59
A2	1.17	1.37
b	0.99	1.40
b1	0.99	1.35
b2	1.65	2.39
b3	1.65	2.34
b4	2.59	3.43
b5	2.59	3.38
С	0.38	0.89
c1	0.38	0.84
D	19.71	20.70
D1	13.08	-

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46	BSC	
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62 BSC		
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

- <sup>(1)</sup> Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")



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